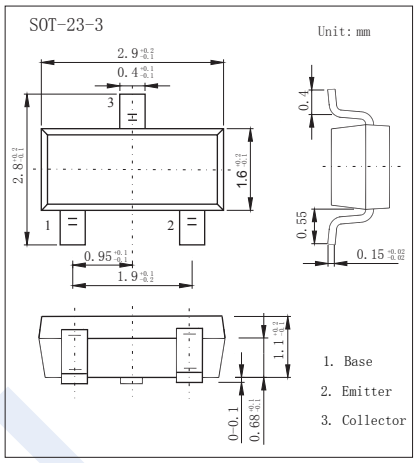
PNP Transistors

2SA1434



■ Features

- Adoption of FBET process.
- High DC current gain (h_{FE}=500 to 1200).
- Low collector-to-emitter saturation voltage ($V_{CE}(sat) \leqslant 0.5V$).
- High V_{EBO} ($V_{EBO} \geqslant 15V$).

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-15	V
Collector current	I_C	-100	mA
Collector current (pulse)	I_{cp}	-200	mA
Collector dissipation	P_C	200	mW
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E=0	-60			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1mA, R_{BE}=∞	-50			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A, I_C=0	-15			
Collector-base cut-off current	I_{CBO}	V_{CB}= -40V , I_E=0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB}= -10V , I_C=0			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-50 mA, I_B=- 1mA		-0.2	-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-10 uA, I_B=- 1mA		-0.8	-1.1	
DC current gain	h_{FE}	V_{CE}= -5V, I_C= -10mA	500	800	1200	
Common base output capacitance	C_{ob}	V_{CB}= -10V, f=1MHz		4.8		pF
Transition frequency	f_T	V_{CB}= -10V,I_C=-10mA		100		MHz

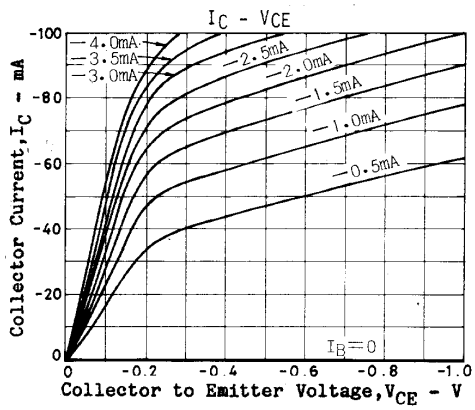
■ Marking

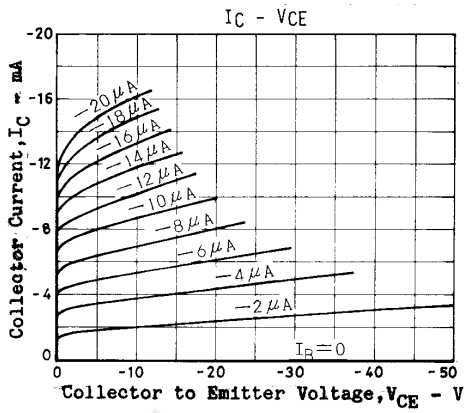
Marking	FL

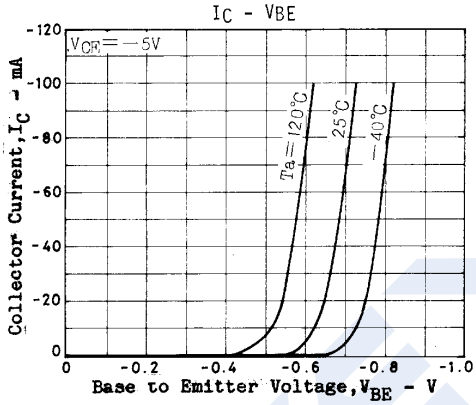
PNP Transistors

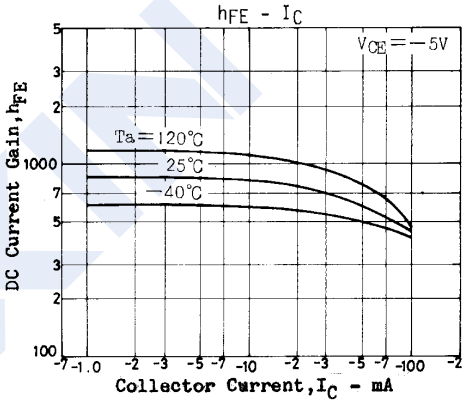
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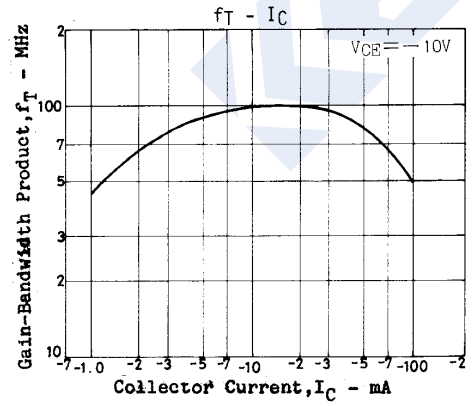
■ Typical Characterisitics

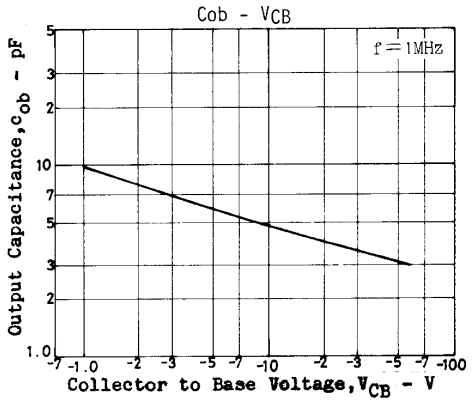


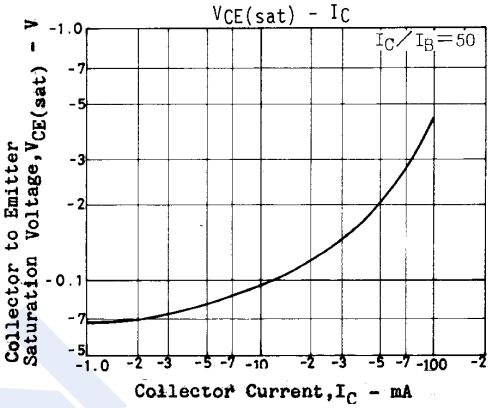


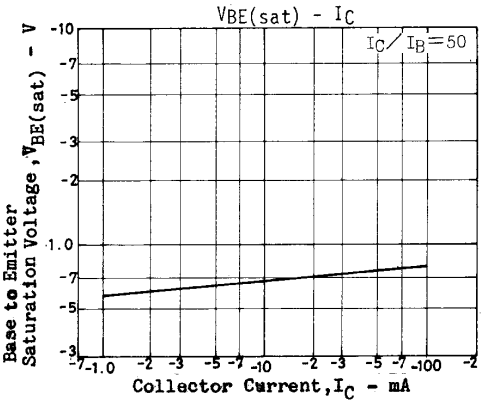












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■ Typical Characterisitics

